

FEATURED PRODUCT

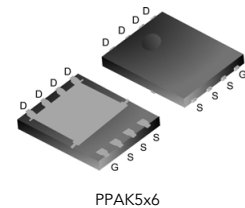
Good-Ark Semiconductor GSGP2R608

80V, 170A, 2.2mΩ, N-Channel SGT MOSFET in PPAK5x6 Package

Good-Ark Semiconductor introduces GSGP2R608, a 80V, 170A, N-Channel SGT MOSFET with industry's lowest $R_{DS(ON)}$ of 2.2mΩ (typ.), $Q_{gd}=17nC$ @ $I_D=50A$, $V_{GS}=10V$. This device utilizes the latest split-gate technology (SGT) and advanced clip bonding techniques to achieve industry's leading figure of merit (FOM) performance with minimized conduction loss. Packaged in the compact PPAK5x6 package with outstanding power dissipation capability, GSGP2R608 is designed to meet the demand of space constraint applications that require higher power density and optimal efficiency. Ideal for synchronous rectifications in 5G telecom, server power supply, battery power drivers and adapters and BLDC motors. The GSGP2R608 reduces the number of MOSFETs in parallel, which increases the overall system reliability while achieving cost saving.

FEATURES

- Best-in-class on-resistance (typical 2.2mΩ)
- High current density and efficiency
- Lower gate-charge
- Industry leading figure of merit (FOM)



BENEFITS

- Small footprint and higher power density
- Reduces the number of MOSFETs in parallel
- Increases system reliability while achieving cost-saving

APPLICATIONS

- BMS
- High frequency switch
- Synchronous rectification
- BLDC motor
- Load switch

Free samples available for immediate testing.

Contact us at: (+1) 631-319-1858 or

inquiry@goodarksemi.com

KEY SPECIFICATIONS

Part Number	I_D	V_{DS}	V_{GS}	$V_{GS(TH)}$ @ $V_{DS}=V_{GS}$, $I_D=250\mu A$		$R_{DS(ON)}$ @ $I_D=50A$, $V_{GS}=10V$		Q_{GD} @ $V_{DD}=40V$, $I_D=50A$, $V_{GS}=10V$	Q_G @ $V_{DD}=40V$, $I_D=50A$, $V_{GS}=10V$	C_{iss}	T_J, T_{STG}
	Max (A)	Max (V)	Max (V)	Min (V)	Max (V)	Typ. (mΩ)	Max (mΩ)	Typ. (nC)	Typ. (nC)	(pF)	(°C)
GSGP2R608	170	80	±20	2.1	3.9	2.2	2.6	17	95	6022	-55 to +150

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